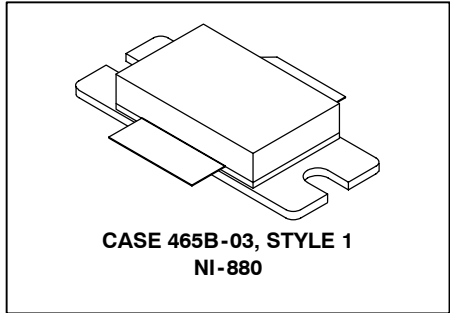


The RF Sub-Micron MOSFET Line
RF Power Field Effect Transistor
N-Channel Enhancement-Mode Lateral MOSFET

MRF19125R3

1990 MHz, 125 W, 26 V
LATERAL N-CHANNEL
RF POWER MOSFET



Designed for PCN and PCS base station applications with frequencies from 1.9 to 2.0 GHz. Suitable for TDMA, CDMA and multicarrier amplifier applications.

- Typical 2-Carrier N-CDMA Performance for $V_{DD} = 26$ Volts, $I_{DQ} = 1300$ mA, $f_1 = 1958.75$ MHz, $f_2 = 1961.25$ MHz IS-95 CDMA (Pilot, Sync, Paging, Traffic Codes 8 Through 13) 1.2288 MHz Channel Bandwidth Carrier. Adjacent Channels Measured over a 30 kHz Bandwidth at $f_1 - 885$ kHz and $f_2 + 885$ kHz. Distortion Products Measured over 1.2288 MHz Bandwidth at $f_1 - 2.5$ MHz and $f_2 + 2.5$ MHz. Peak/Avg. = 9.8 dB @ 0.01% Probability on CCDF.
 Output Power — 24 Watts Avg.
 Power Gain — 13.6 dB
 Efficiency — 22%
 ACPR — -51 dB
 IM3 — -37.0 dBc
- Internally Matched, Controlled Q, for Ease of Use
- High Gain, High Efficiency and High Linearity
- Integrated ESD Protection
- Designed for Maximum Gain and Insertion Phase Flatness
- Capable of Handling 5:1 VSWR, @ 26 Vdc, 1990 MHz, 125 Watts (CW) Output Power
- Excellent Thermal Stability
- Characterized with Series Equivalent Large-Signal Impedance Parameters
- In Tape and Reel. R3 Suffix = 250 Units per 56 mm, 13 inch Reel.

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Drain-Source Voltage	V_{DSS}	65	Vdc
Gate-Source Voltage	V_{GS}	-0.5, +15	Vdc
Total Device Dissipation @ $T_C = 25^\circ\text{C}$ Derate above 25°C	P_D	330 1.89	Watts $\text{W}/^\circ\text{C}$
Storage Temperature Range	T_{stg}	-65 to +150	$^\circ\text{C}$
Operating Junction Temperature	T_J	200	$^\circ\text{C}$

THERMAL CHARACTERISTICS

Characteristic	Symbol	Value (1)	Unit
Thermal Resistance, Junction to Case	$R_{\theta JC}$	0.53	$^\circ\text{C}/\text{W}$

ESD PROTECTION CHARACTERISTICS

Test Conditions	Class
Human Body Model	2 (Minimum)
Machine Model	M3 (Minimum)

(1) Refer to AN1955/D, *Thermal Measurement Methodology of RF Power Amplifiers*. Go to <http://www.motorola.com/semiconductors/rf>. Select Documentation/Application Notes - AN1955.

NOTE - CAUTION - MOS devices are susceptible to damage from electrostatic charge. Reasonable precautions in handling and packaging MOS devices should be observed.

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ELECTRICAL CHARACTERISTICS (T_C = 25°C unless otherwise noted)

Characteristic	Symbol	Min	Typ	Max	Unit
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OFF CHARACTERISTICS

Drain-Source Breakdown Voltage (V _{GS} = 0 Vdc, I _D = 100 μAdc)	V _{(BR)DSS}	65	—	—	Vdc
Gate-Source Leakage Current (V _{GS} = 5 Vdc, V _{DS} = 0 Vdc)	I _{GSS}	—	—	1	μAdc
Zero Gate Voltage Drain Leakage Current (V _{DS} = 26 Vdc, V _{GS} = 0 Vdc)	I _{DSS}	—	—	10	μAdc

ON CHARACTERISTICS

Forward Transconductance (V _{DS} = 10 Vdc, I _D = 3 Adc)	g _{fs}	—	9	—	S
Gate Threshold Voltage (V _{DS} = 10 Vdc, I _D = 300 μAdc)	V _{GS(th)}	2	—	4	Vdc
Gate Quiescent Voltage (V _{DS} = 26 Vdc, I _D = 1300 mA)	V _{GS(Q)}	2.5	3.9	4.5	Vdc
Drain-Source On-Voltage (V _{GS} = 10 Vdc, I _D = 3 Adc)	V _{DS(on)}	—	0.185	0.21	Vdc

DYNAMIC CHARACTERISTICS

Reverse Transfer Capacitance (1) (V _{DS} = 26 Vdc, V _{GS} = 0, f = 1 MHz)	C _{rss}	—	5.4	—	pF
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FUNCTIONAL TESTS (In Motorola Test Fixture) 2-Carrier N-CDMA, 1.2288 MHz Channel Bandwidth Carriers. Peak/Avg = 9.8 dB @ 0.01% Probability on CCDF.

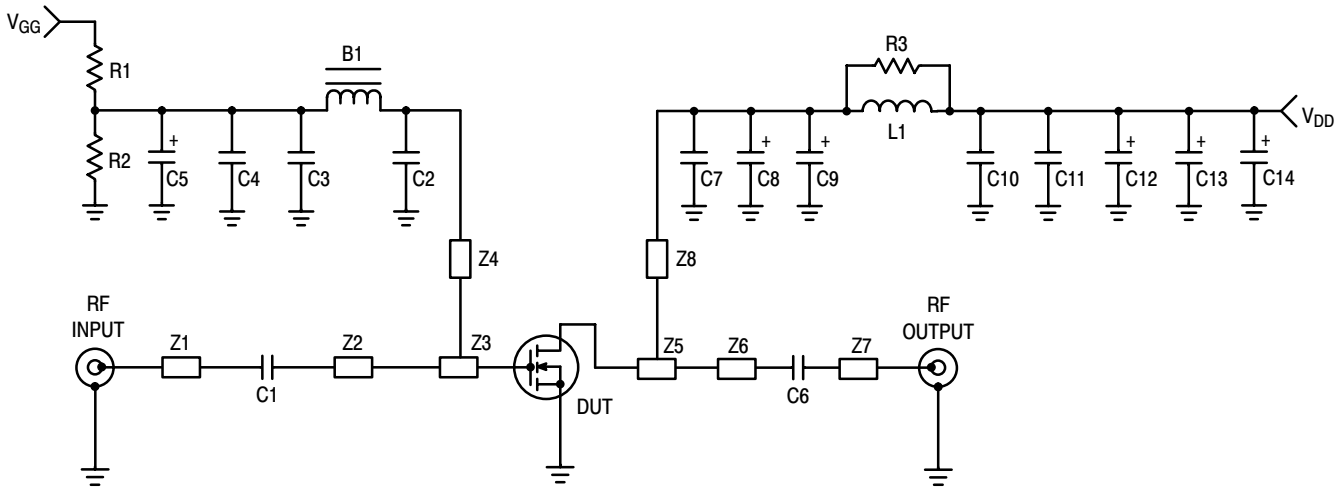
Common-Source Amplifier Power Gain (V _{DD} = 26 Vdc, P _{out} = 24 W Avg, I _{DQ} = 1300 mA, f ₁ = 1930 MHz, f ₂ = 1932.5 MHz and f ₁ = 1987.5 MHz, f ₂ = 1990 MHz)	G _{ps}	12	13.5	—	dB
Drain Efficiency (V _{DD} = 26 Vdc, P _{out} = 24 W Avg, I _{DQ} = 1300 mA, f ₁ = 1930 MHz, f ₂ = 1932.5 MHz and f ₁ = 1987.5 MHz, f ₂ = 1990 MHz)	η	19	22	—	%
Intermodulation Distortion (V _{DD} = 26 Vdc, P _{out} = 24 W Avg, I _{DQ} = 1300 mA, f ₁ = 1930 MHz, f ₂ = 1932.5 MHz and f ₁ = 1987.5 MHz, f ₂ = 1990 MHz; IM3 measured over 1.2288 MHz Bandwidth at f ₁ -2.5 MHz and f ₂ +2.5 MHz)	IMD	—	-37	-35	dBc
Adjacent Channel Power Ratio (V _{DD} = 26 Vdc, P _{out} = 24 W Avg, I _{DQ} = 1300 mA, f ₁ = 1930 MHz, f ₂ = 1932.5 MHz and f ₁ = 1987.5 MHz, f ₂ = 1990 MHz; ACPR measured over 30 kHz Bandwidth at f ₁ -885 MHz and f ₂ +885 MHz)	ACPR	—	-51	-47	dBc
Input Return Loss (V _{DD} = 26 Vdc, P _{out} = 24 W Avg, I _{DQ} = 1300 mA, f ₁ = 1930 MHz, f ₂ = 1932.5 MHz and f ₁ = 1987.5 MHz, f ₂ = 1990 MHz)	IRL	—	-13	-9	dB
Output Mismatch Stress (V _{DD} = 26 Vdc, P _{out} = 125 W CW, I _{DQ} = 1300 mA, f = 1930 MHz, VSWR = 5:1, All Phase Angles at Frequency of Test)	Ψ	No Degradation In Output Power Before and After Test			

(1) Part is internally matched both on input and output.

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ELECTRICAL CHARACTERISTICS — continued ($T_C = 25^\circ\text{C}$ unless otherwise noted)

Characteristic	Symbol	Min	Typ	Max	Unit
FUNCTIONAL TESTS (In Motorola Test Fixture)					
Two-Tone Common-Source Amplifier Power Gain ($V_{DD} = 26\text{ Vdc}$, $P_{out} = 125\text{ W PEP}$, $I_{DQ} = 1300\text{ mA}$, $f_1 = 1930\text{ MHz}$, $f_2 = 1990\text{ MHz}$, Tone Spacing = 100 kHz)	G_{ps}	—	13.5	—	dB
Two-Tone Drain Efficiency ($V_{DD} = 26\text{ Vdc}$, $P_{out} = 125\text{ W PEP}$, $I_{DQ} = 1300\text{ mA}$, $f_1 = 1930\text{ MHz}$, $f_2 = 1990\text{ MHz}$, Tone Spacing = 100 kHz)	η	—	35	—	%
Third Order Intermodulation Distortion ($V_{DD} = 26\text{ Vdc}$, $P_{out} = 125\text{ W PEP}$, $I_{DQ} = 1300\text{ mA}$, $f_1 = 1930\text{ MHz}$, $f_2 = 1990\text{ MHz}$, Tone Spacing = 100 kHz)	IMD	—	-30	—	dBc
Input Return Loss ($V_{DD} = 26\text{ Vdc}$, $P_{out} = 125\text{ W PEP}$, $I_{DQ} = 1300\text{ mA}$, $f_1 = 1930\text{ MHz}$, $f_2 = 1990\text{ MHz}$, Tone Spacing = 100 kHz)	IRL	—	-13	—	dB
$P_{out, 1\text{ dB Compression Point}}$ ($V_{DD} = 26\text{ Vdc}$, $I_{DQ} = 1300\text{ mA}$, $f = 1990\text{ MHz}$)	P1dB	—	130	—	W



Z1, Z7	0.500" x 0.084" Microstrip	Board	0.030" Glass Teflon [®] ,
Z2	1.105" x 0.084" Microstrip		Keene GX-0300-55-22, $\epsilon_r = 2.55$
Z3	0.360" x 0.895" Microstrip	PCB	Etched Circuit Boards
Z4	0.920" x 0.048" Microstrip		MRF19125 Rev. 5, CMR
Z5	0.605" x 1.195" Microstrip		
Z6	0.800" x 0.084" Microstrip		
Z8	0.660" x 0.095" Microstrip		

Figure 1. MRF19125 Test Circuit Schematic

Table 1. MRF19125 Test Circuit Component Designations and Values

Designators	Description
B1	Short Ferrite Bead, Fair Rite #2743019447
C1	51 pF Chip Capacitor, ATC #100B510JCA500X
C2, C7	5.1 pF Chip Capacitors, ATC #100B5R1JCA500X
C3, C10	1000 pF Chip Capacitors, ATC #100B102JCA500X
C4, C11	0.1 μ F Chip Capacitors, Kemet #CDR33BX104AKWS
C5	0.1 μ F Tantalum Chip Capacitor, Kemet #T491C105M050
C6	10 pF Chip Capacitor, ATC #100B100JCA500X
C8	10 μ F Tantalum Chip Capacitor, Kemet #T491X106K035AS4394
C9, C12, C13, C14	22 μ F Tantalum Chip Capacitors, Kemet #T491X226K035AS4394
L1	1 Turn, #20 AWG, 0.100" ID, Motorola
N1, N2	Type N Flange Mounts, Omni Spectra #3052-1648-10
R1	1.0 k Ω , 1/8 W Chip Resistor
R2	220 k Ω , 1/8 W Chip Resistor
R3	10 Ω , 1/8 W Chip Resistor

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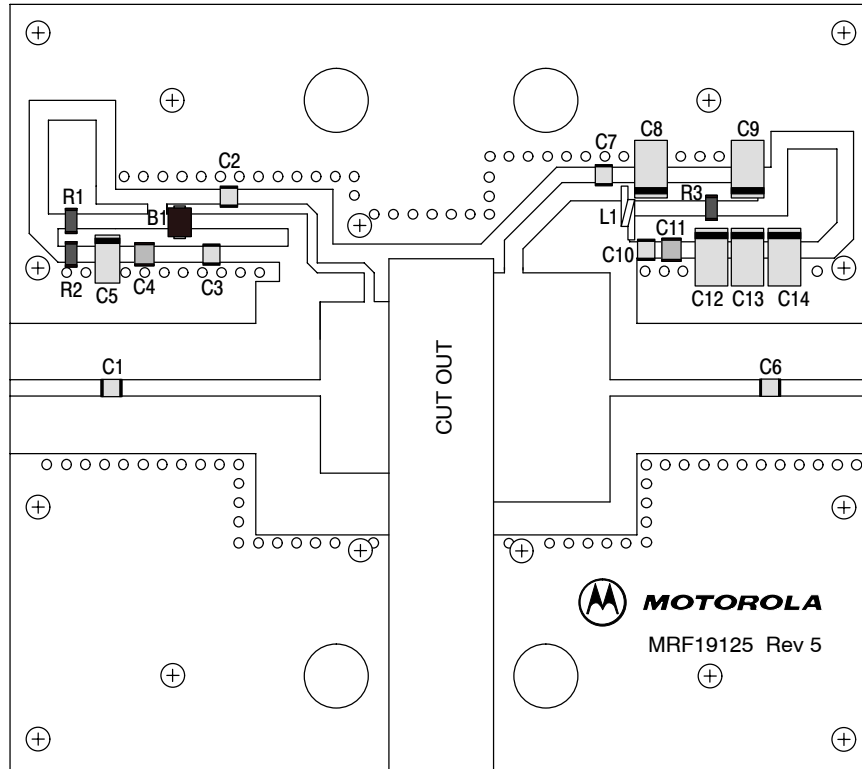


Figure 2. MRF19125 Test Circuit Component Layout

TYPICAL CHARACTERISTICS

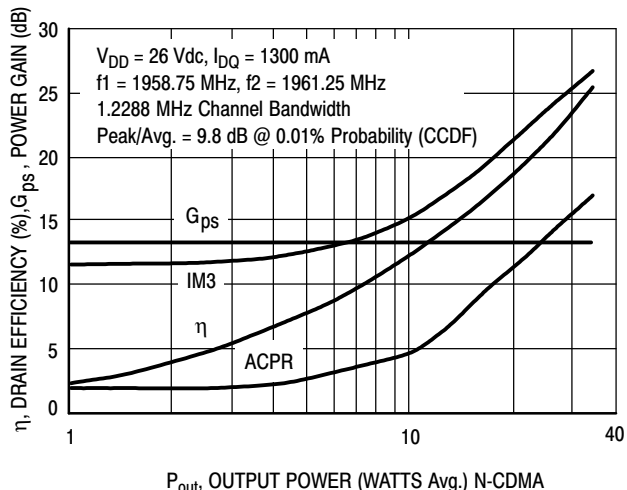


Figure 3. 2-Carrier CDMA ACPR, IM3, Power Gain and Drain Efficiency versus Output Power

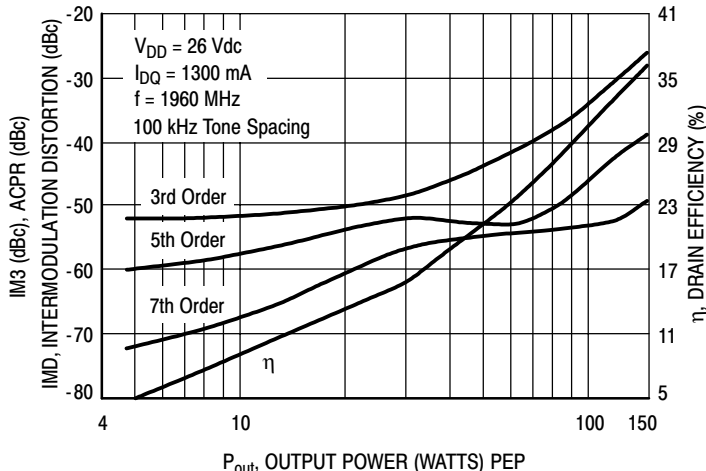


Figure 4. Intermodulation Distortion Products versus Output Power

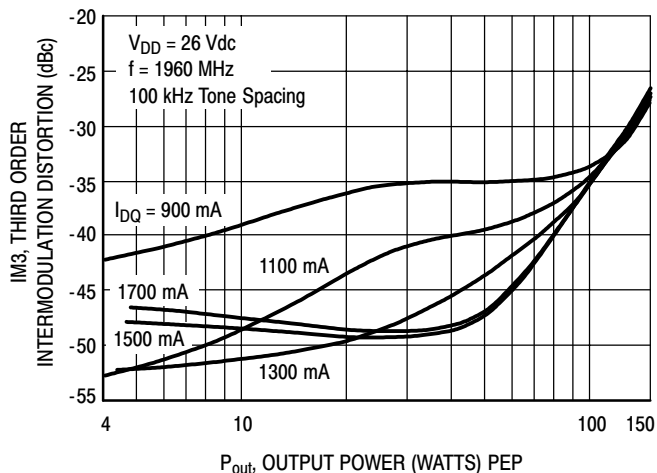


Figure 5. Third Order Intermodulation Distortion versus Output Power

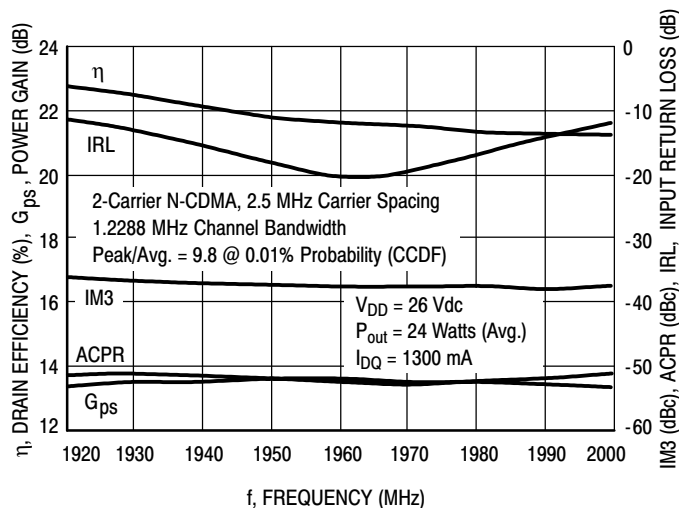


Figure 6. 2-Carrier N-CDMA Broadband Performance

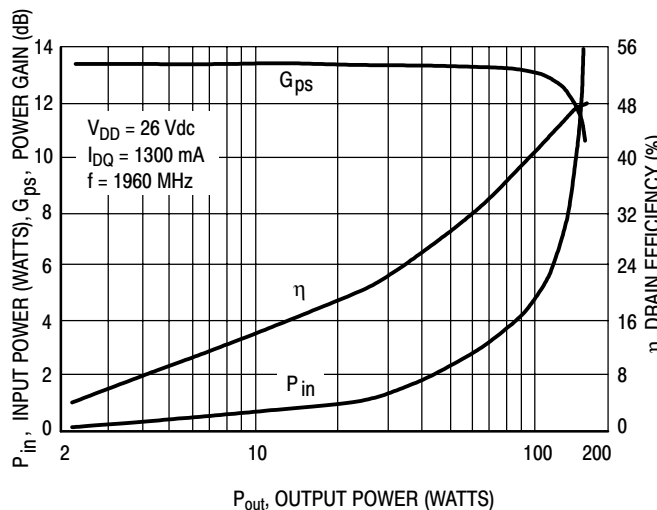


Figure 7. CW Performance

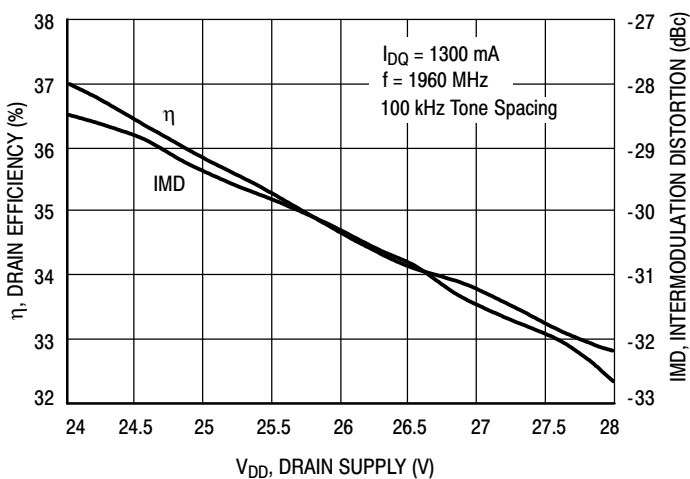


Figure 8. Two-Tone Intermodulation Distortion and Drain Efficiency versus Drain Supply

TYPICAL CHARACTERISTICS

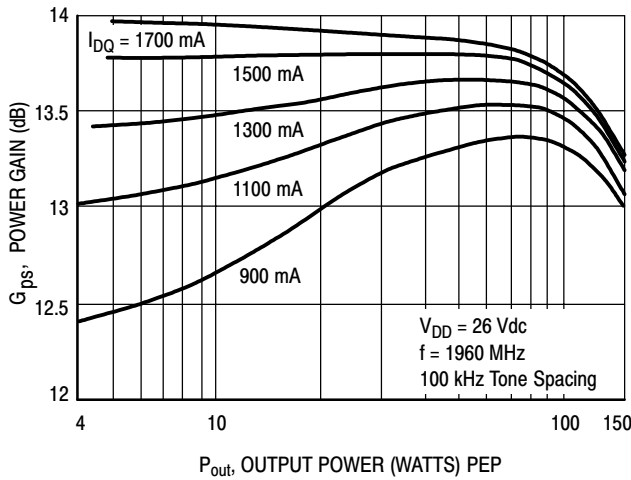


Figure 9. Two-Tone Power Gain versus Output Power

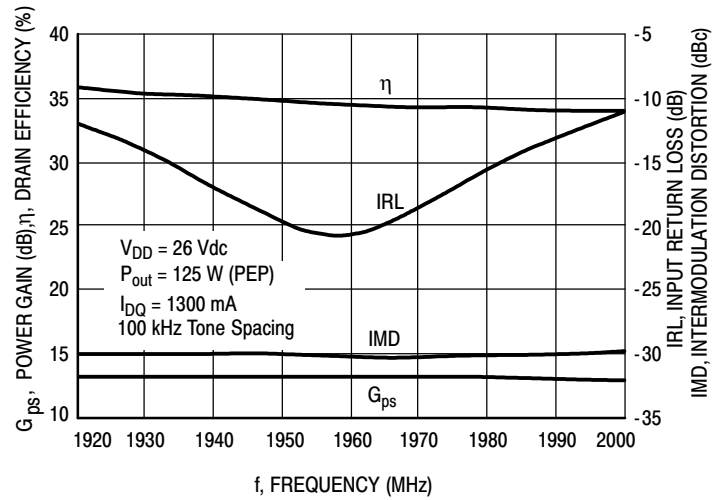


Figure 10. Two-Tone Broadband Performance

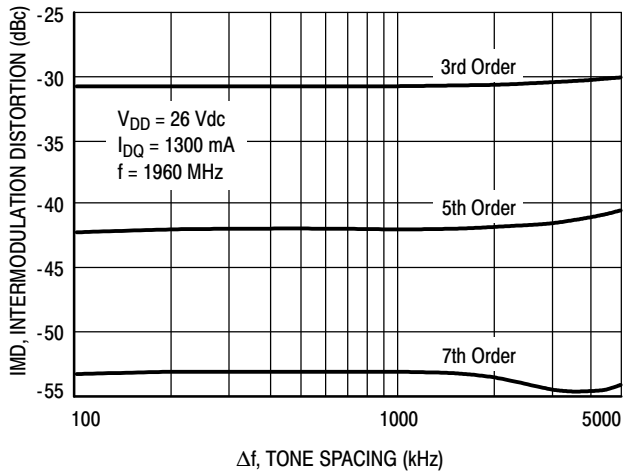


Figure 11. Intermodulation Distortion Products versus Two-Tone Tone Spacing

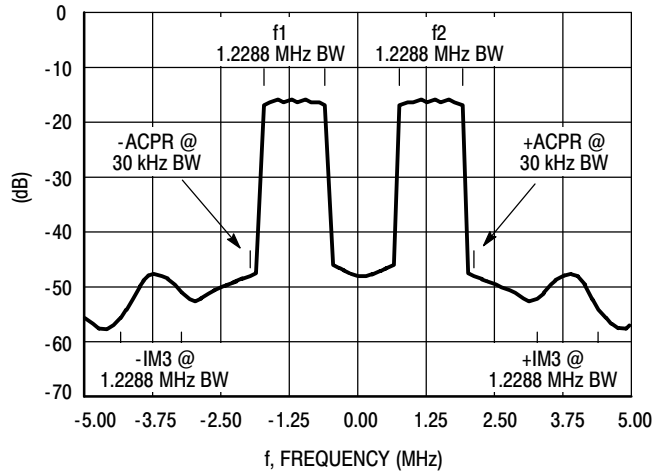
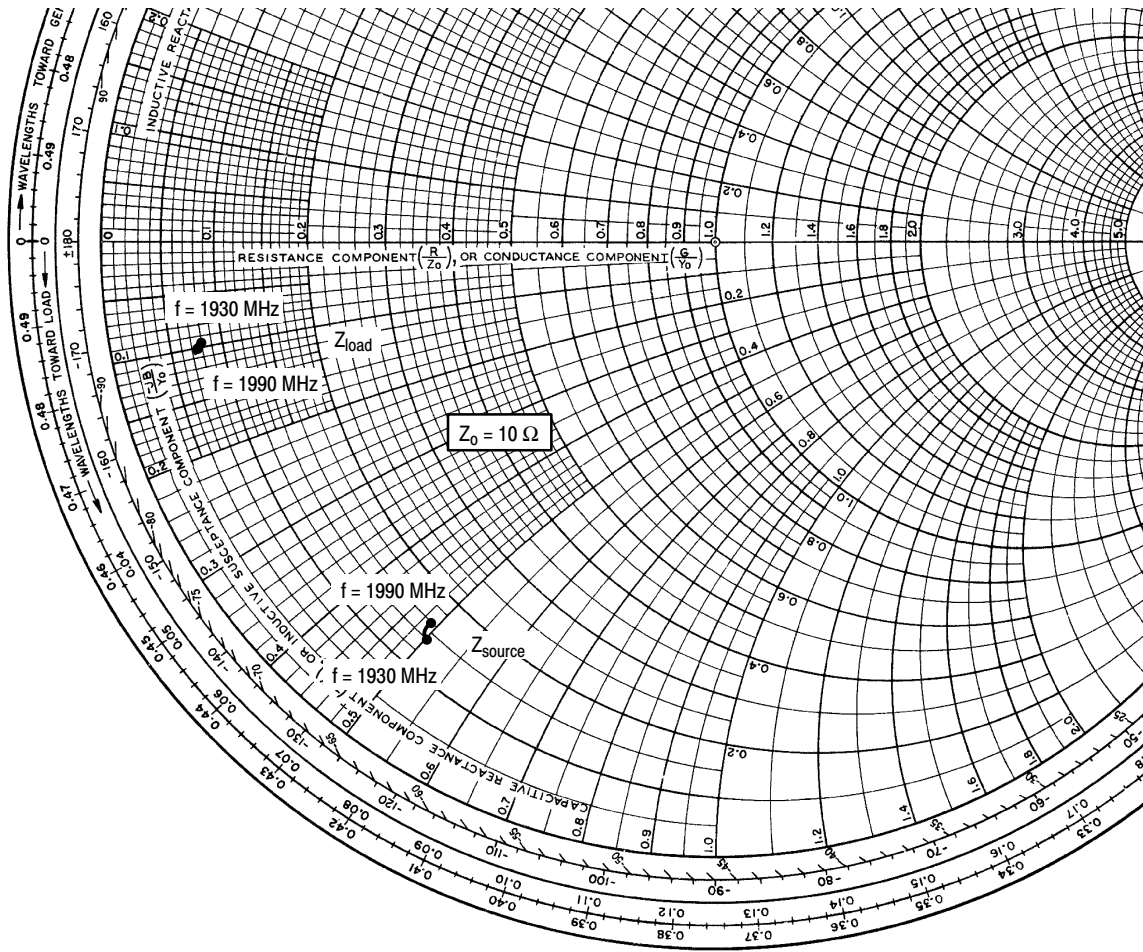


Figure 12. 2-Carrier N-CDMA Spectrum



$V_{DD} = 26\text{ V}$, $I_{DQ} = 1300\text{ mA}$, $P_{out} = 24\text{ W (Avg.)}$

f MHz	Z_{source} Ω	Z_{load} Ω
1930	1.43 - j5.01	0.75 - j0.93
1960	1.51 - j4.88	0.71 - j0.89
1990	1.56 - j4.93	0.68 - j1.02

Z_{source} = Test circuit impedance as measured from gate to ground.

Z_{load} = Test circuit impedance as measured from drain to ground.

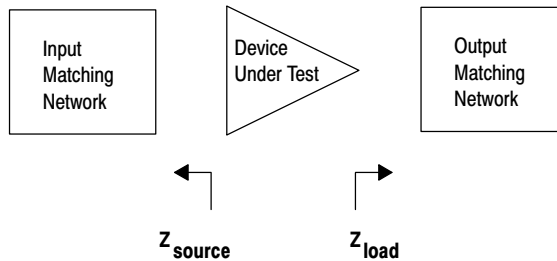


Figure 13. Series Equivalent Input and Output Impedance

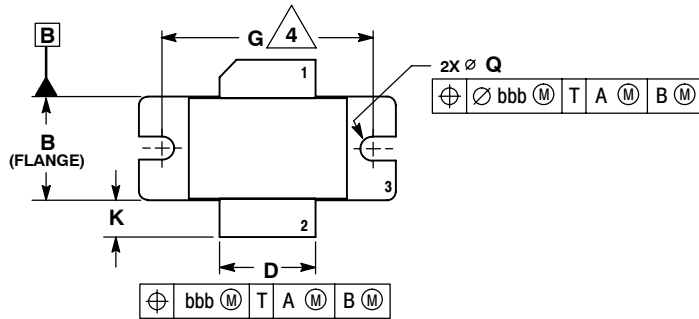
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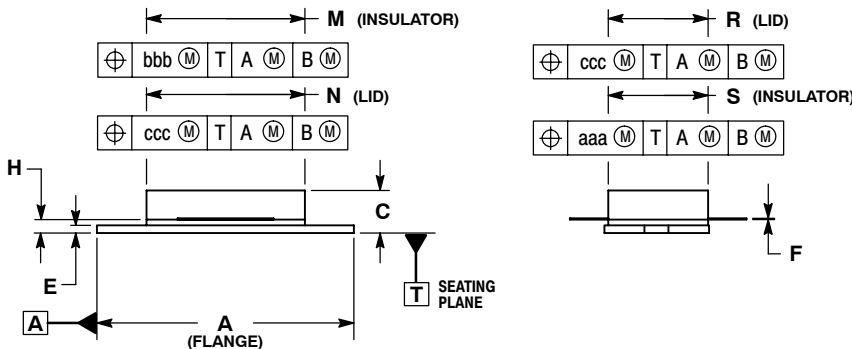
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PACKAGE DIMENSIONS



- NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M-1994.
 2. CONTROLLING DIMENSION: INCH.
 3. DIMENSION H IS MEASURED 0.030 (0.762) AWAY FROM PACKAGE BODY.
 4. RECOMMENDED BOLT CENTER DIMENSION OF 1.16 (29.57) BASED ON M3 SCREW.

DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	1.335	1.345	33.91	34.16
B	0.535	0.545	13.6	13.8
C	0.147	0.200	3.73	5.08
D	0.495	0.505	12.57	12.83
E	0.035	0.045	0.89	1.14
F	0.003	0.006	0.08	0.15
G	1.100 BSC		27.94 BSC	
H	0.057	0.067	1.45	1.70
K	0.175	0.205	4.44	5.21
M	0.872	0.888	22.15	22.55
N	0.871	0.889	19.30	22.60
Q	Ø.118	Ø.138	Ø3.00	Ø3.51
R	0.515	0.525	13.10	13.30
S	0.515	0.525	13.10	13.30
aaa		0.007 REF		0.178 REF
bbb		0.010 REF		0.254 REF
ccc		0.015 REF		0.381 REF



**CASE 465B-03
ISSUE C
NI-880**

STYLE 1:
PIN 1. DRAIN
2. GATE
3. SOURCE

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